

2N7002BK 60 V, 350 mA N-channel Trench MOSFET Rev. 1 — 17 June 2010

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1.Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-	60	V
V _{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	$T_{amb} = 25 \text{ °C};$ $V_{GS} = 10 \text{ V}$	<u>[1]</u> -	-	350	mA
R _{DSon}	drain-source on-state resistance	T _j = 25 °C; V _{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 350 mA N-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	S	source		D
3	D	drain	1 2	G
				017aaa000

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
2N7002BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
2N7002BK	LN*
[1] * = -: made in Hong Kong	

- * = p: made in Hong Kong
- * = t: made in Malaysia
- * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V _{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	V _{GS} = 10 V	[1]		
		T _{amb} = 25 °C	-	350	mA
		T _{amb} = 100 °C	-	245	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$	-	1.2	A

Product data sheet

2N7002BK

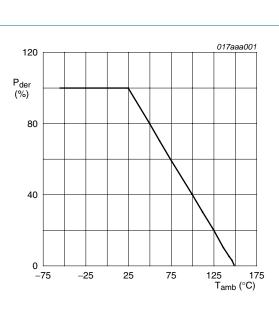
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Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	370	mW
			<u>[1]</u> -	440	mW
		T _{sp} = 25 °C	-	1.2	W
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
Source-d	rain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> -	350	mA
ESD max	imum rating				
V_{ESD}	electrostatic discharge voltage	human body model	<u>[3]</u> _	2000	V

Limiting values ... continued Table 5.

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



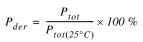
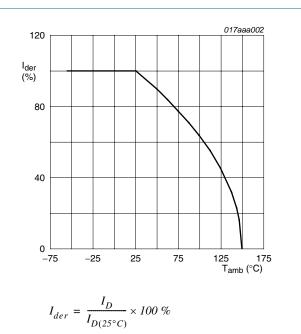


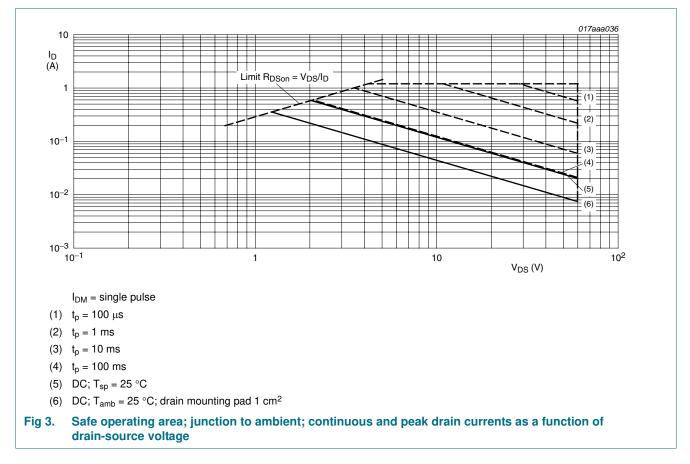
Fig 1. Normalized total power dissipation as a function of ambient temperature





2N7002BK

60 V, 350 mA N-channel Trench MOSFET



6. Thermal characteristics

Table 6.Thermal characteristics

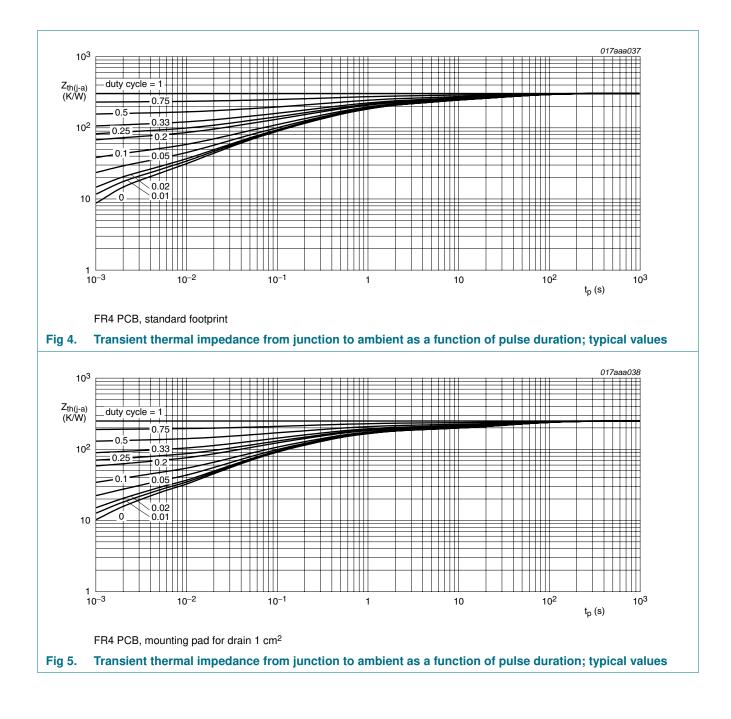
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	295	340	K/W
			[2] _	250	285	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	105	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

2N7002BK

60 V, 350 mA N-channel Trench MOSFET



60 V, 350 mA N-channel Trench MOSFET

7. Characteristics

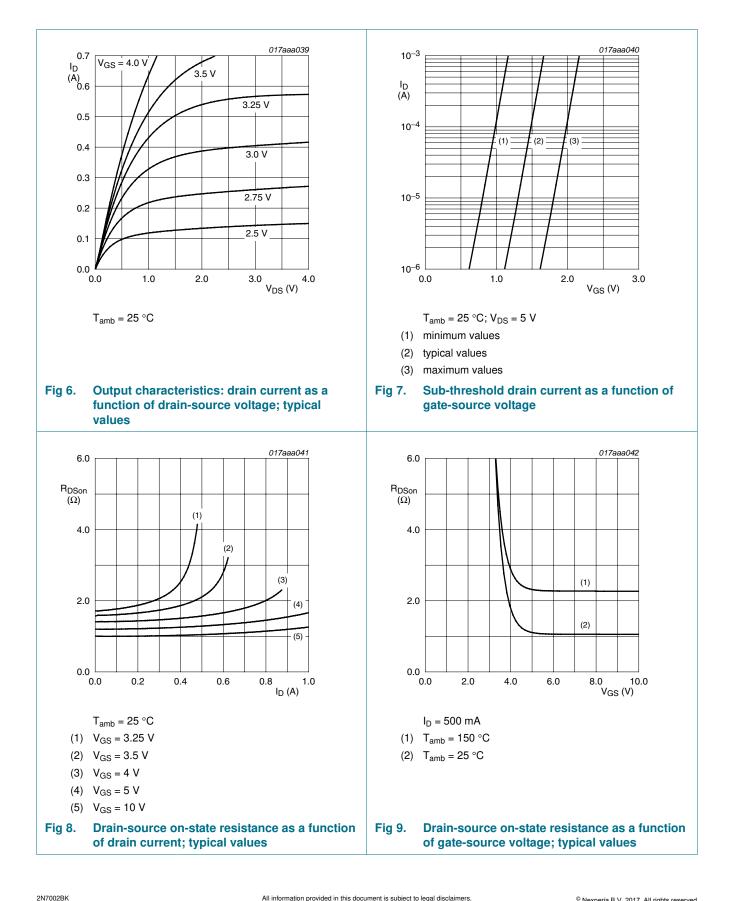
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \ \mu\text{A}; \ V_{GS} = 0 \ V$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μA
		T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS}=\pm 20~V;~V_{DS}=0~V$	-	-	10	μA
R _{DSon} drain-source o resistance	drain-source on-state		<u>[1]</u>			
	resistance	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 50 \text{ mA}$	-	1.3	2	Ω
		V_{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	550	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I _D = 300 mA;	-	0.5	0.6	nC
Q _{GS}	gate-source charge	V _{DS} = 30 V; V _{GS} = 4.5 V	-	0.2	-	nC
Q _{GD}	gate-drain charge	$-v_{\rm GS} = 4.5 v$	-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 10 V;$	-	33	50	pF
C _{oss}	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	V _{DD} = 50 V;	-	5	10	ns
t _r	rise time	R _L = 250 Ω; - V _{GS} = 10 V;	-	6	-	ns
t _{d(off)}	turn-off delay time	$-v_{GS} = 10 v;$ $R_G = 6 \Omega$	-	12	24	ns
t _f	fall time	_ ~	-	7	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V	0.47	0.75	1.1	V

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Product data sheet

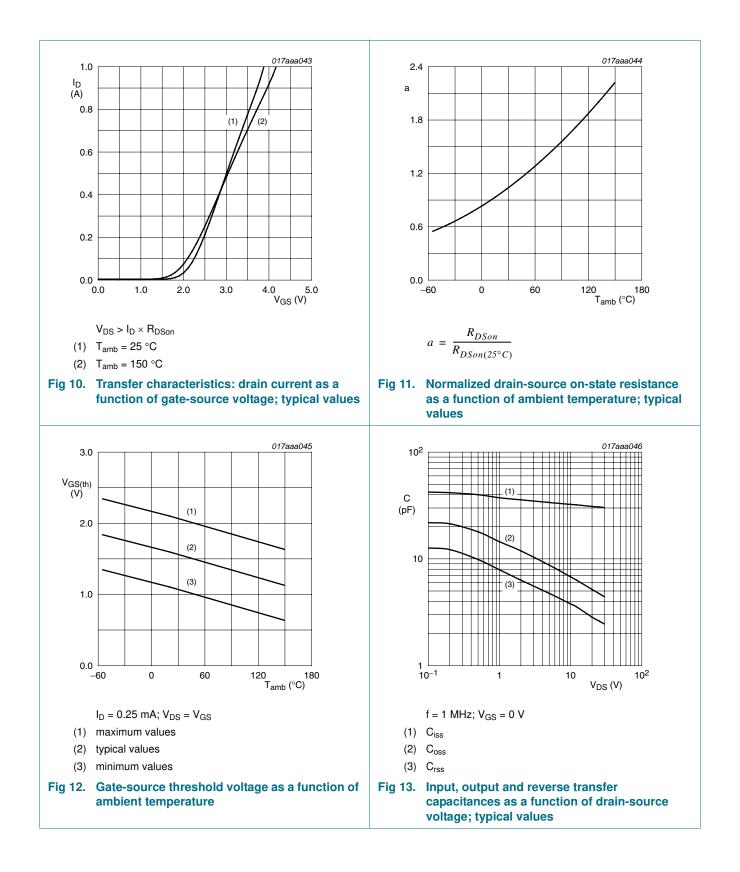
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60 V, 350 mA N-channel Trench MOSFET



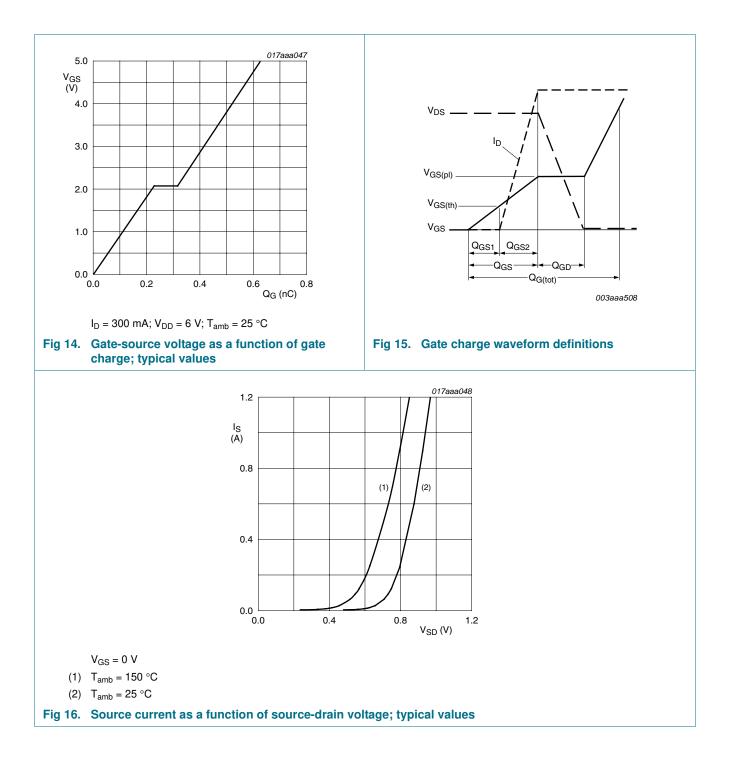
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60 V, 350 mA N-channel Trench MOSFET



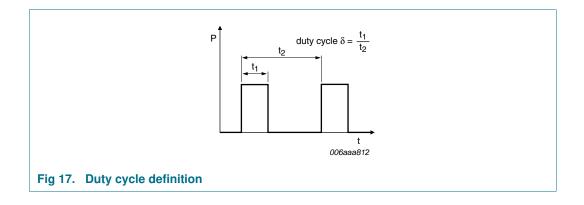
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60 V, 350 mA N-channel Trench MOSFET



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8. Test information



60 V, 350 mA N-channel Trench MOSFET

9. Package outline

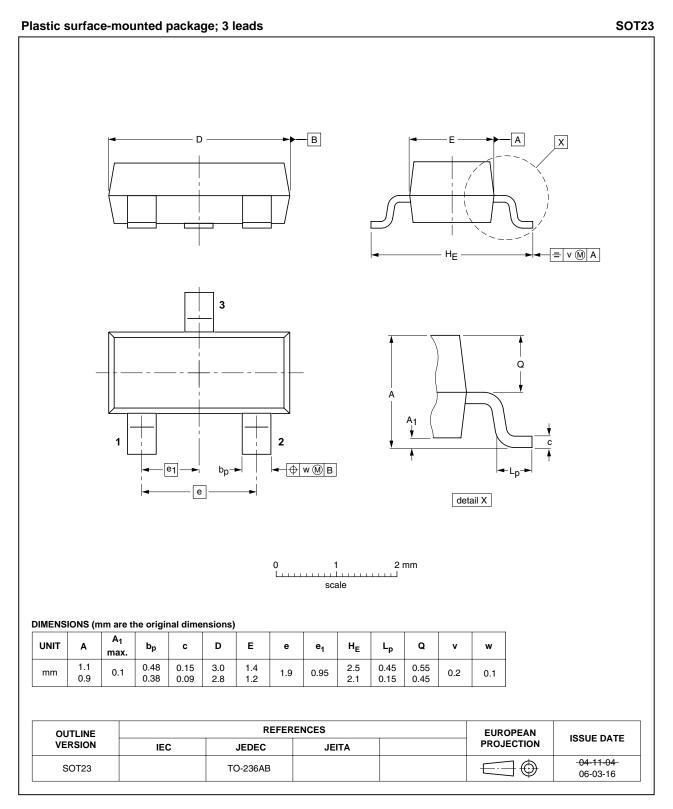
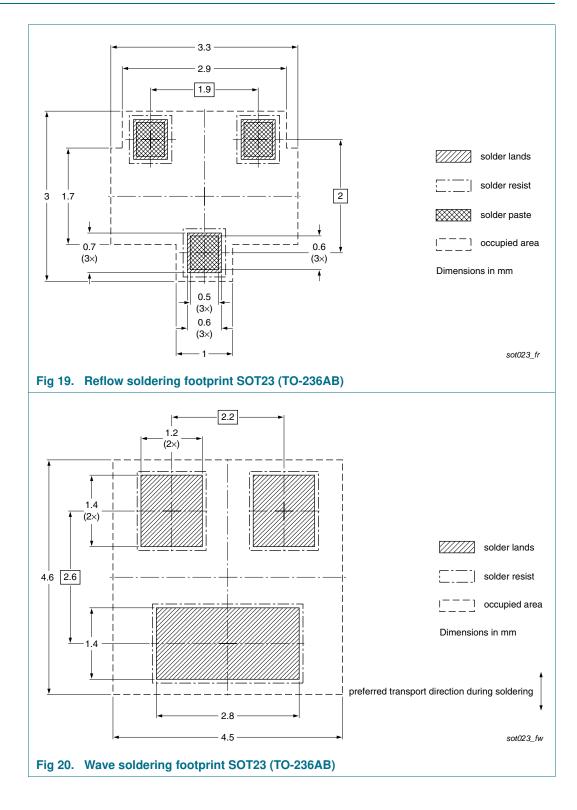


Fig 18. Package outline SOT23 (TO-236AB)

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60 V, 350 mA N-channel Trench MOSFET

10. Soldering



60 V, 350 mA N-channel Trench MOSFET

11. Revision history

Table 8. Re	Revision history					
Document ID	Release	date Data sheet status	S Change notice	Supersedes		
2N7002BK v.1	2010061	7 Product data shee	et -	-		

60 V, 350 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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60 V, 350 mA N-channel Trench MOSFET

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60 V, 350 mA N-channel Trench MOSFET

14. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 4
7	Characteristics
8	Test information 10
9	Package outline 11
10	Soldering 12
11	Revision history 13
12	Legal information 14
12.1	Data sheet status 14
12.2	Definitions 14
12.3	Disclaimers 14
12.4	Trademarks
13	Contact information 15
14	Contents 16